

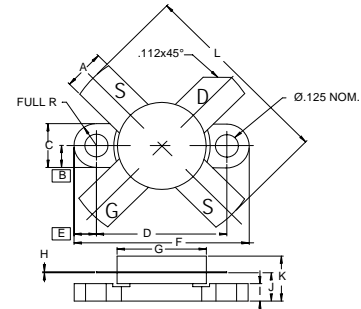
HF/VHF POWER MOS TRANSISTOR

DESCRIPTION:

The **ASI BLF177** is a N-Channel Enhancement-Mode MOSFET RF Power Transistor Designed for industrial and military applications in the HF/ VHF frequency range.

MAXIMUM RATINGS

I_D	16 A
V_{DS}	110 V
V_{GS}	±20 V
P_{DISS}	220 W @ T _{mb} = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.8 °C/W

PACKAGE STYLE .500 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I _D = 50 mA	110			V
I_{DSS}	V _{DS} = 50 V V _{GS} = 0 V			2.5	mA
I_{GSS}	V _{DS} = 0 V V _{GS} = ±20 V			1.0	μA
V_{GS(th)}	I _D = 50 mA V _{DS} = 10 V	2.0		4.5	V
ΔV_{GS}	I _D = 50 mA V _{DS} = 10 V			100	mV
g_{fs}	I _D = 5.0 A V _{DS} = 10 V	4.5	6.2		S
R_{DS(on)}	I _D = 5.0 A V _{DS} = 10 V		0.2	0.3	Ω
I_{DSX}	V _{GS} = 10 V V _{DS} = 10 V		25		A
C_{is}	V _{DS} = 50 V V _{GS} = 0 V f = 1.0 MHz		480		pF
C_{os}			190		
C_{rs}			14		